

MOSFET – Dual, N-Channel, Asymmetric, POWERTRENCH[®], Power Clip, 30 V FDPC5018SG

General Description

This device includes two specialized N-Channel MOSFETs in a dual package. The switch node has been internally connected to enable easy placement and routing of synchronous buck converters. The control MOSFET (Q1) and synchronous SyncFET™ (Q2) have been designed to provide optimal power efficiency.

Features

Q1: N-Channel

- Max $R_{DS(on)}$ = 5.0 mΩ at V_{GS} = 10 V, I_D = 17 A
- Max $R_{DS(on)}$ = 6.5 mΩ at V_{GS} = 4.5 V, I_D = 14 A

Q2: N-Channel

- Max $R_{DS(on)}$ = 1.6 mΩ at V_{GS} = 10 V, I_D = 32 A
- Max $R_{DS(on)}$ = 2.0 mΩ at V_{GS} = 4.5 V, I_D = 28 A
- Low Inductance Packaging Shortens Rise/Fall Times, Resulting in Lower Switching Losses.
- MOSFET Integration Enables Optimum Layout for Lower Circuit Inductance and Reduced Switch Node Ringing.
- ESD Protection Level: HBM > 500 V, CDM > 1 kV, MM > 100 V
- RoHS Compliant

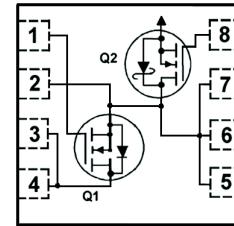
Applications

- Computing
- Communications
- General Purpose Point of Load

Table 1. PIN DESCRIPTION

Pin	Name	Description
1	HSG	High Side Gate
2	GR	Gate Return
3, 4, 9	V+(HSD)	High Side Drain
5, 6, 7	SW	Switching Node, Low Side Drain
8	LSG	Low Side Gate
10	GND (LSS)	Low Side Source

ELECTRICAL CONNECTION



N-Channel MOSFET

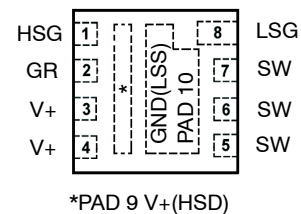


Top View

Bottom View

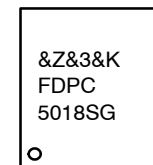
Power Clip 56
(PQFN8 5x6)
CASE 483AR

PIN ASSIGNMENT



*PAD 9 V+(HSD)

MARKING DIAGRAM



&Z = Assembly Plant Code
&3 = Date Code (Year & Week)
&K = Lot Traceability Code
FDPC5018SG = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 11 of this data sheet.

FDPC5018SG

MOSFET MAXIMUM RATINGS (T_A = 25°C, Unless otherwise noted.)

Symbol	Parameter	Q1	Q2	Unit
V _{DS}	Drain to Source Voltage	30	30	V
Bvdsst	Bvdsst (Transient) < 100 ns	32.5	32.5	V
V _{GS}	Gate to Source Voltage	±20	±12	V
I _D	Drain Current – Continuous (T _C = 25°C) (Note 5)	56	109	A
	– Continuous (T _C = 100°C) (Note 5)	35	69	
	– Continuous (T _A = 25°C)	17 (Note 1a)	32 (Note 1b)	
	– Pulsed (T _A = 25°C) (Note 4)	227	704	
E _{AS}	Single Pulsed Avalanche Energy (Note 3)	54	181	mJ
P _D	Power Dissipation for Single Operation (T _C = 25°C) (T _A = 25°C) (T _A = 25°C)	23 2.1 (Note 1a) 1.0 (Note 1c)	29 2.3 (Note 1b) 1.1 (Note 1d)	W
T _J , T _{STG}	Operating and Storage Junction Temperature Range	–55 to +150		°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Q1	Q2	Unit
R _{θJC}	Thermal Resistance, Junction to Case	5.6	4.3	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	60 (Note 1a)	55 (Note 1b)	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	130 (Note 1c)	120 (Note 1d)	°C/W

Table 2. ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted.)

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
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OFF CHARACTERISTICS

BV _{DSS}	Drain to Source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0 V I _D = 1 mA, V _{GS} = 0 V	Q1 Q2	30 30	– –	– –	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, referenced to 25°C I _D = 10 mA, referenced to 25°C	Q1 Q2	– –	15 19	– –	mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V V _{DS} = 24 V, V _{GS} = 0 V	Q1 Q2	– –	– –	1 500	μA μA
I _{GSS}	Gate to Source Leakage Current, Forward	V _{GS} = 20 V, V _{DS} = 0 V V _{GS} = 12 V, V _{DS} = 0 V	Q1 Q2	– –	– –	100 100	nA nA

ON CHARACTERISTICS

V _{GS(th)}	Gate to Source Threshold Voltage	V _{GS} = V _{DS} , I _D = 250 μA V _{GS} = V _{DS} , I _D = 1 mA	Q1 Q2	1.0 1.0	1.7 1.6	3.0 3.0	V
ΔV _{GS(th)} / ΔT _J	Gate to Source Threshold Voltage Temperature Coefficient	I _D = 250 μA, referenced to 25°C I _D = 10 mA, referenced to 25°C	Q1 Q2	– –	–5 –3	– –	mV/°C
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 10 V, I _D = 17 A V _{GS} = 4.5 V, I _D = 14 A V _{GS} = 10 V, I _D = 17 A, T _J = 125°C	Q1	– –	4.1 5.4 5.7	5.0 6.5 7.0	mΩ
		V _{GS} = 10 V, I _D = 32 A V _{GS} = 4.5 V, I _D = 28 A V _{GS} = 10 V, I _D = 32 A, T _J = 125°C	Q2	– –	1.4 1.7 2.1	1.6 2.0 2.4	
g _{FS}	Forward Transconductance	V _{DS} = 5 V, I _D = 17 A V _{DS} = 5 V, I _D = 32 A	Q1 Q2	– –	93 188	– –	S

FDPC5018SG

Table 2. ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted.)(continued)

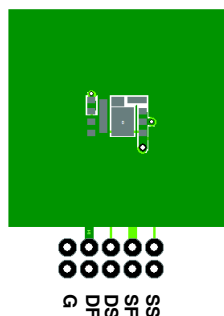
Symbol	Parameter	Test Conditions		Type	Min	Typ	Max	Units
DYNAMIC CHARACTERISTICS								
C _{iSS}	Input Capacitance	Q1: V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz Q2: V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		Q1	–	1224	1715	pF
C _{oSS}	Output Capacitance			Q2	–	4593	6430	pF
C _{rSS}	Reverse Transfer Capacitance			Q1	–	397	560	pF
R _g	Gate Resistance			Q2	–	1210	1695	pF
				Q1	–	42	60	pF
				Q2	–	80	115	pF
				Q1	0.1	0.5	1.5	Ω
				Q2	0.1	0.8	2.4	Ω
SWITCHING CHARACTERISTICS								
t _{d(on)}	Turn-On Delay Time	Q1: V _{DD} = 15 V, I _D = 17 A, R _{GEN} = 6 Ω Q2: V _{DD} = 15 V, I _D = 32 A, R _{GEN} = 6 Ω		Q1	–	8	16	ns
t _r	Rise Time			Q2	–	14	25	ns
t _{d(off)}	Turn-Off Delay Time			Q1	–	2	10	ns
t _f	Fall Time			Q2	–	5	10	ns
Q _g	Total Gate Charge	V _{GS} = 0 V to 10 V	Q1 V _{DD} = 15 V, I _D = 17 A Q2 V _{DD} = 15 V, I _D = 32 A	Q1	–	18	33	ns
Q _g	Total Gate Charge	V _{GS} = 0 V to 4.5 V		Q2	–	38	61	ns
Q _{gs}	Gate to Source Gate Charge			Q1	–	2	10	ns
Q _{gd}	Gate to Drain “Miller” Charge			Q2	–	4	10	ns
Q _g	Total Gate Charge	V _{GS} = 0 V to 10 V	Q1 V _{DD} = 15 V, I _D = 17 A Q2 V _{DD} = 15 V, I _D = 32 A	Q1	–	17	24	nC
Q _g	Total Gate Charge	V _{GS} = 0 V to 4.5 V		Q2	–	62	87	nC
Q _{gs}	Gate to Source Gate Charge			Q1	–	8	11	nC
Q _{gs}	Gate to Source Gate Charge			Q2	–	28	40	nC
Q _{gd}	Gate to Drain “Miller” Charge			Q1	–	3.1	–	nC
Q _{gd}	Gate to Drain “Miller” Charge			Q2	–	11	–	nC
Q _{gd}	Gate to Drain “Miller” Charge			Q1	–	2.0	–	nC
Q _{gd}	Gate to Drain “Miller” Charge			Q2	–	5.3	–	nC
DRAIN–SOURCE DIODE CHARACTERISTICS								
V _{SD}	Source to Drain Diode Forward Voltage	V _{GS} = 0 V, I _S = 17 A (Note 2) V _{GS} = 0 V, I _S = 32 A (Note 2)		Q1	–	0.8	1.2	V
t _{rr}	Reverse Recovery Time	Q1 I _F = 17 A, di/dt = 100 A/μs Q2 I _F = 32 A, di/dt = 240 A/μs		Q2	–	0.8	1.2	V
Q _{rr}	Reverse Recovery Charge			Q1	–	23	37	ns
				Q2	–	32	51	ns
				Q1	–	8	16	nC
				Q2	–	40	64	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

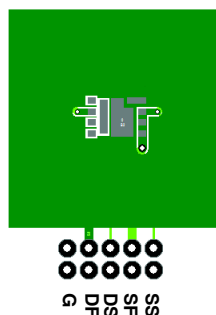
FDPC5018SG

NOTES:

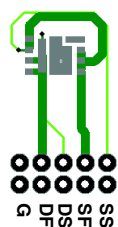
1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 × 1.5 in. board of FR-4 material. $R_{\theta CA}$ is determined by the user's board design.



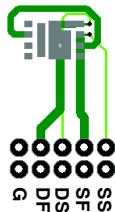
a) 60°C/W when mounted on a 1 in² pad of 2 oz copper.



b) 55°C/W when mounted on a 1 in² pad of 2 oz copper.



c) 130°C/W when mounted on a minimum pad of 2 oz copper.



d) 120°C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μ s, Duty cycle < 2.0%.
3. Q1: EAS of 54 mJ is based on starting $T_J = 25^\circ\text{C}$; L = 3 mH, $I_{AS} = 6$ A, $V_{DD} = 30$ V, $V_{GS} = 10$ V, 100% tested at L = 0.1 mH, $I_{AS} = 20$ A.
Q2: EAS of 181 mJ is based on starting $T_J = 25^\circ\text{C}$; L = 3 mH, $I_{AS} = 11$ A, $V_{DD} = 30$ V, $V_{GS} = 10$ V, 100% tested at L = 0.1 mH, $I_{AS} = 36$ A.
4. Pulsed Id refer to Figure 11 and Figure 24 SOA graphs for more details.
5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

TYPICAL CHARACTERISTICS (Q1 N-CHANNEL)

($T_J = 25^\circ\text{C}$ unless otherwise noted)

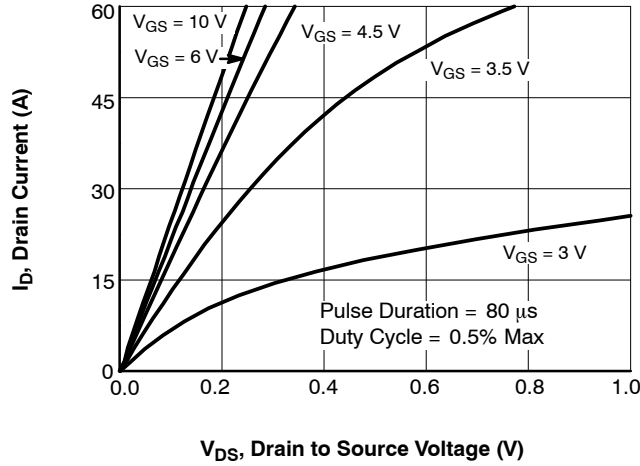


Figure 1. On-Region Characteristics

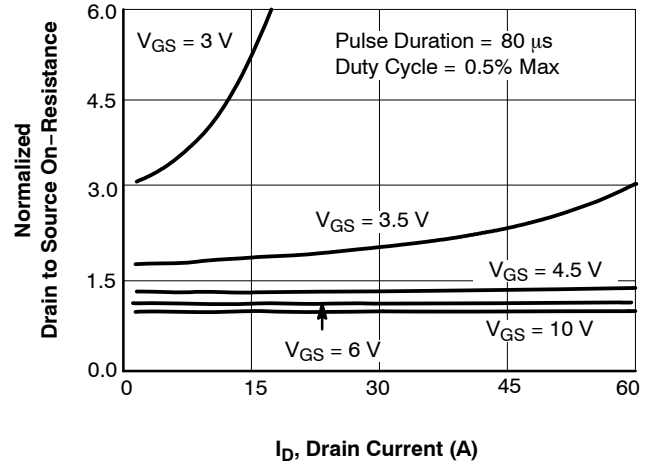


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

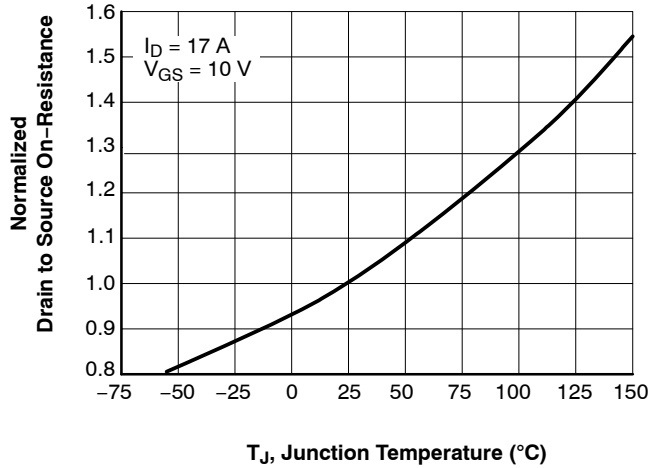


Figure 3. Normalized On-Resistance vs. Junction Temperature

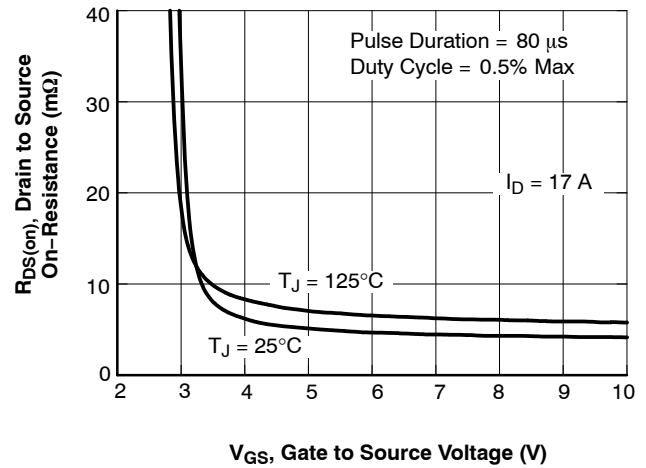


Figure 4. On-Resistance vs. Gate to Source Voltage

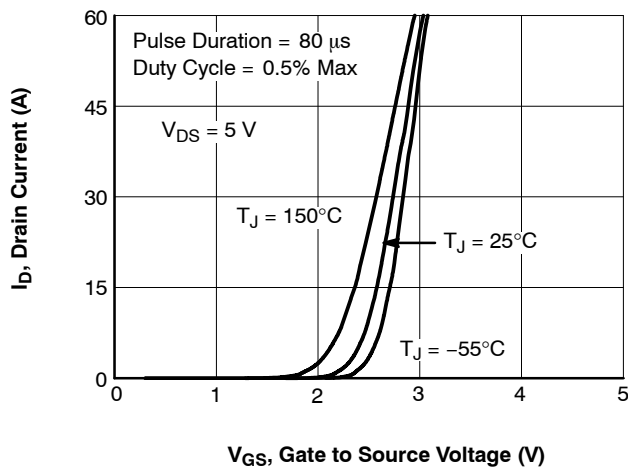


Figure 5. Transfer Characteristics

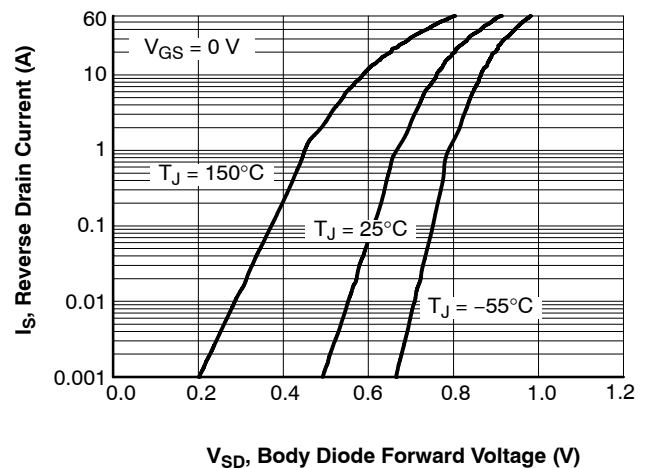


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (Q1 N-CHANNEL)

($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

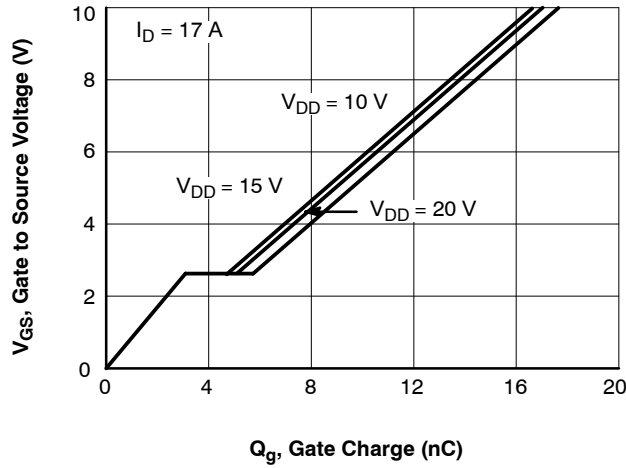


Figure 7. Gate Charge Characteristics

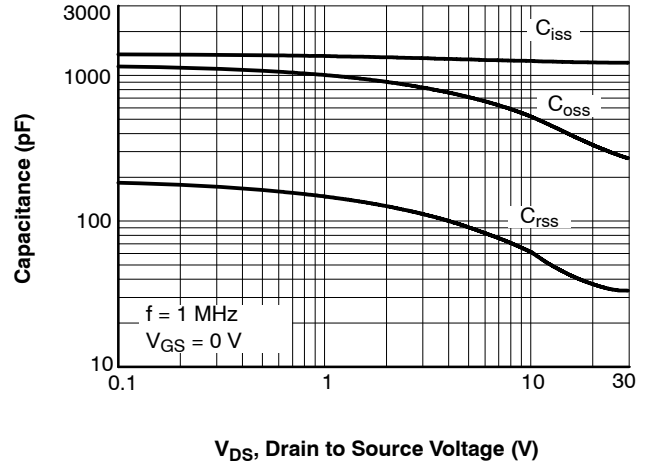


Figure 8. Capacitance vs. Drain to Source Voltage

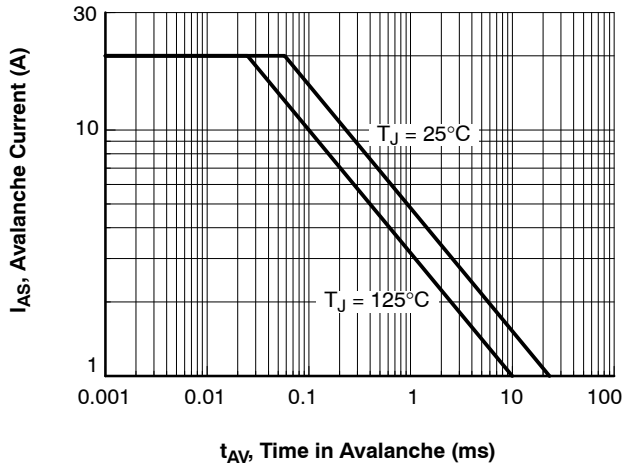


Figure 9. Unclamped Inductive Switching Capability

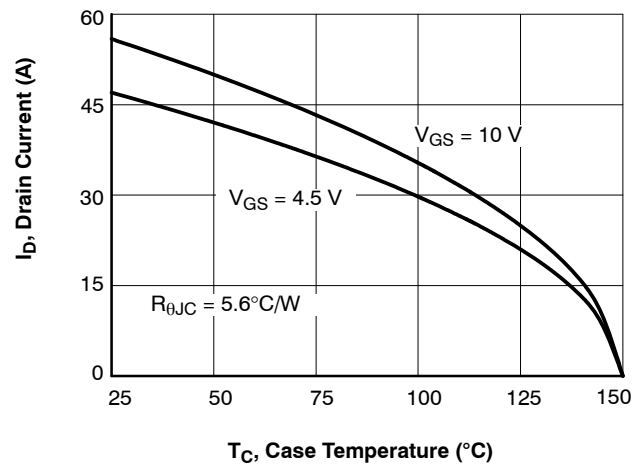


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

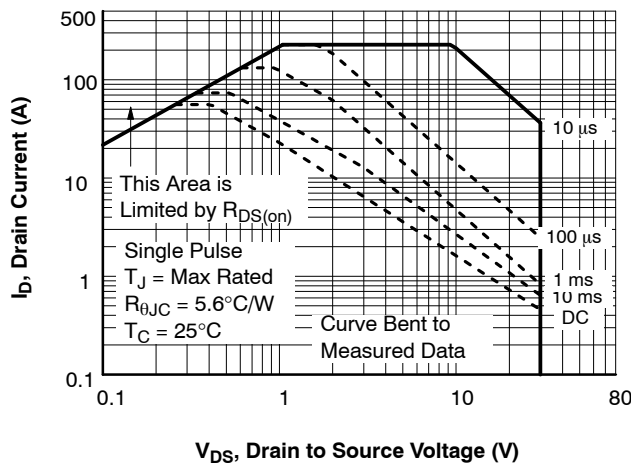


Figure 11. Forward Bias Safe Operating Area

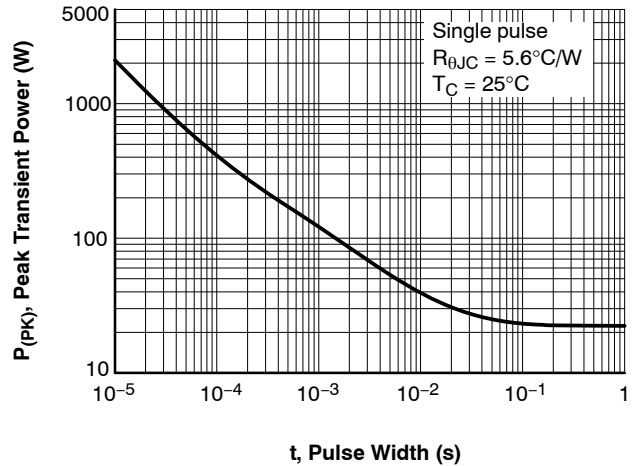


Figure 12. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS (Q1 N-CHANNEL)

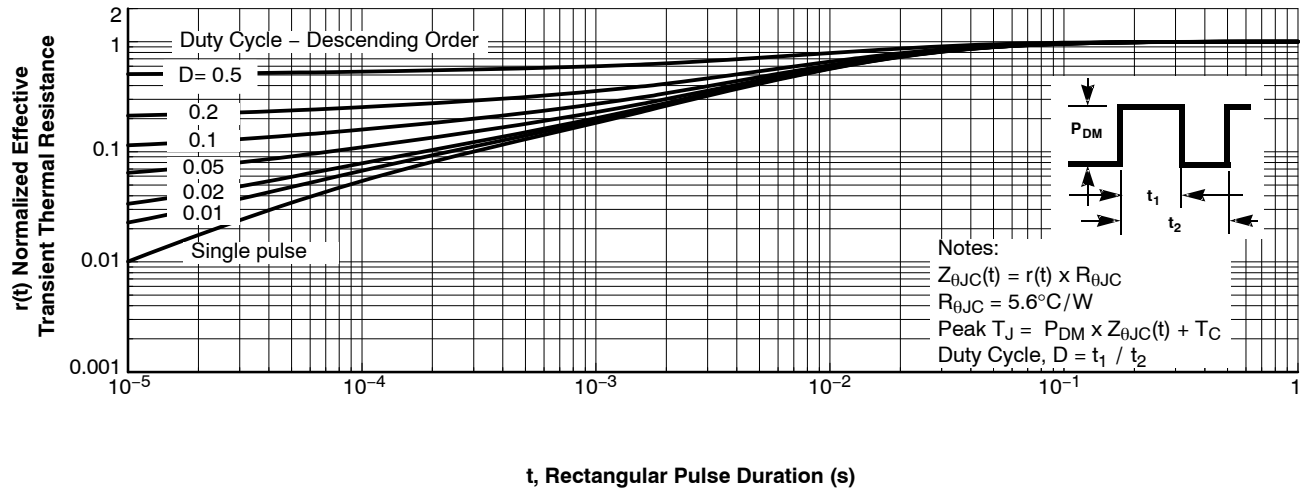
(T_J = 25°C unless otherwise noted) (continued)

Figure 13. Junction-to-Case Transient Thermal Response Curve

TYPICAL CHARACTERISTICS (Q2 N-CHANNEL)

($T_J = 25^\circ\text{C}$ unless otherwise noted)

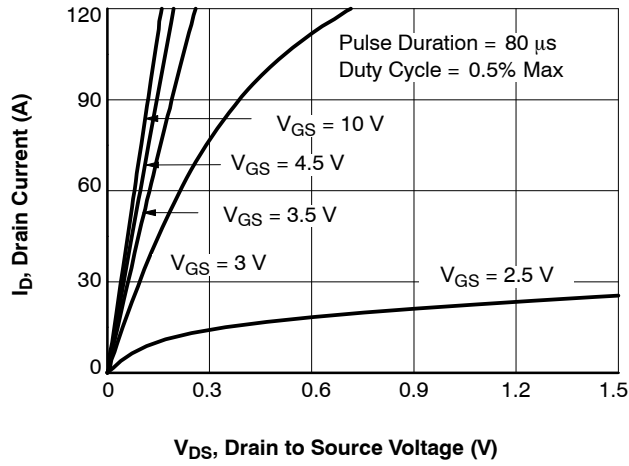


Figure 14. On-Region Characteristics

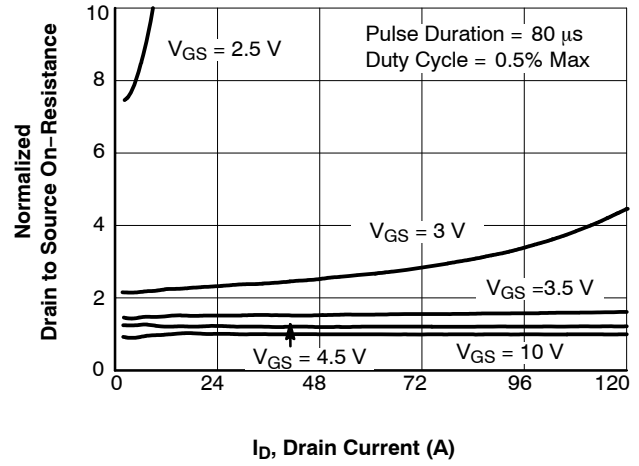


Figure 15. Normalized On-Resistance vs. Drain Current and Gate Voltage

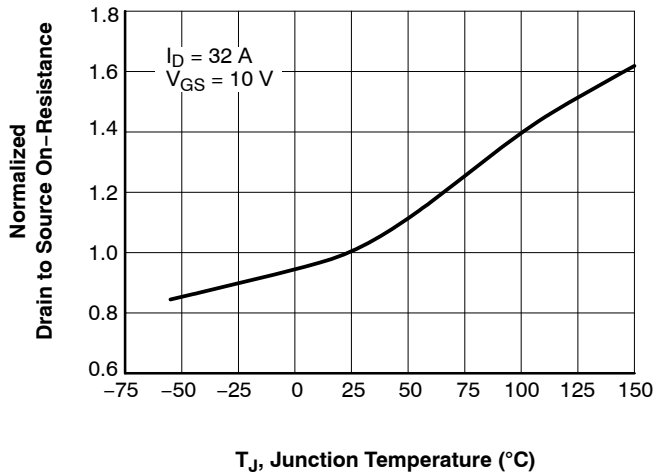


Figure 16. Normalized On-Resistance vs. Junction Temperature

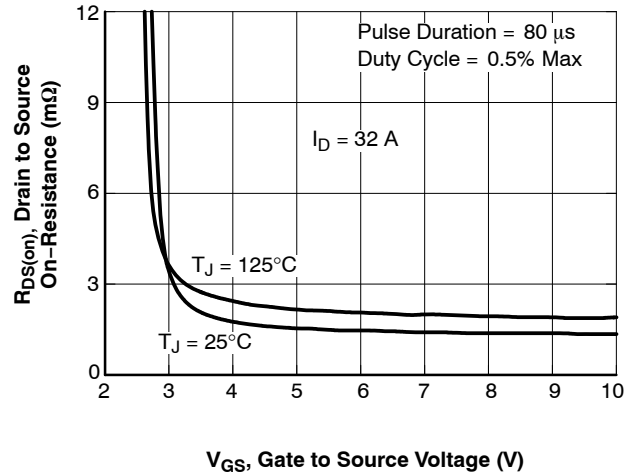


Figure 17. On-Resistance vs. Gate to Source Voltage

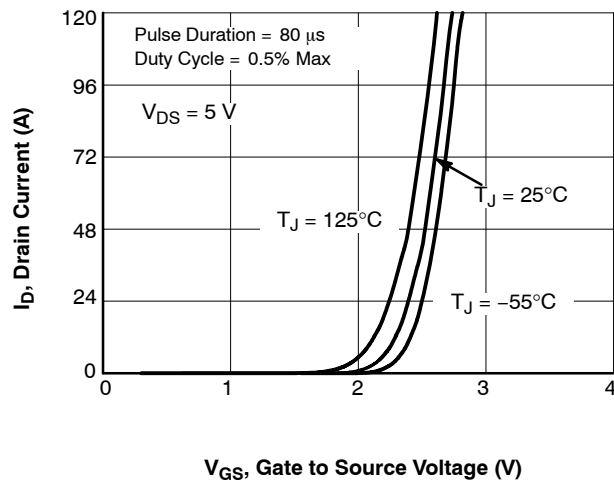


Figure 18. Transfer Characteristics

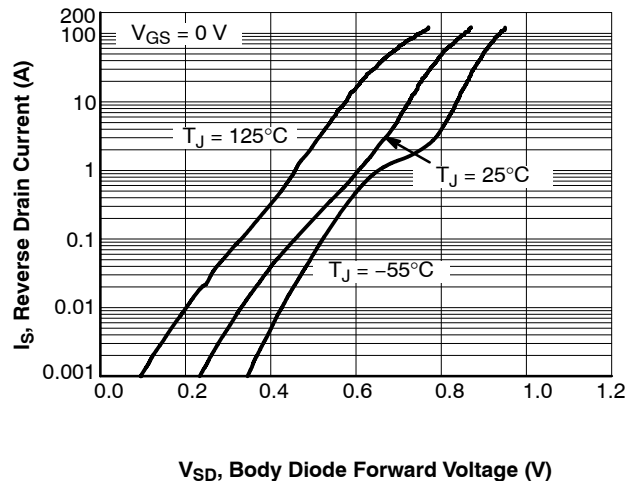


Figure 19. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (Q2 N-CHANNEL)

($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

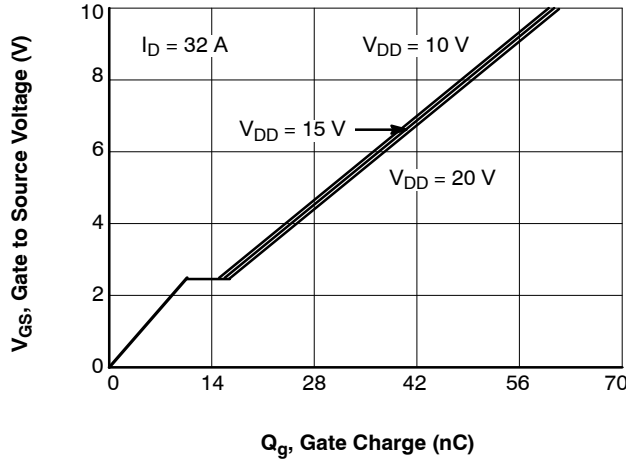


Figure 20. Gate Charge Characteristics

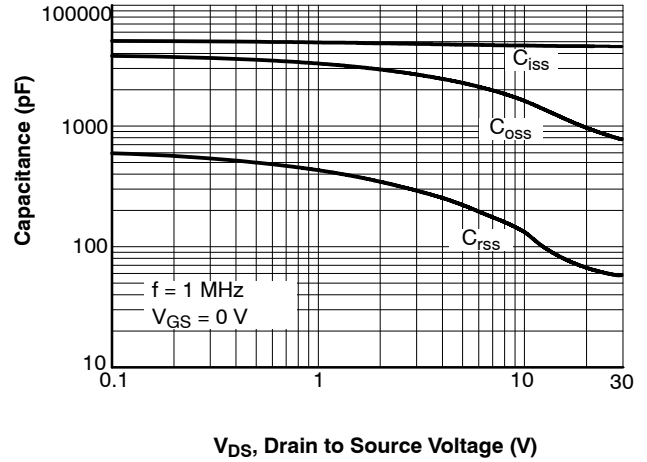


Figure 21. Capacitance vs. Drain to Source Voltage

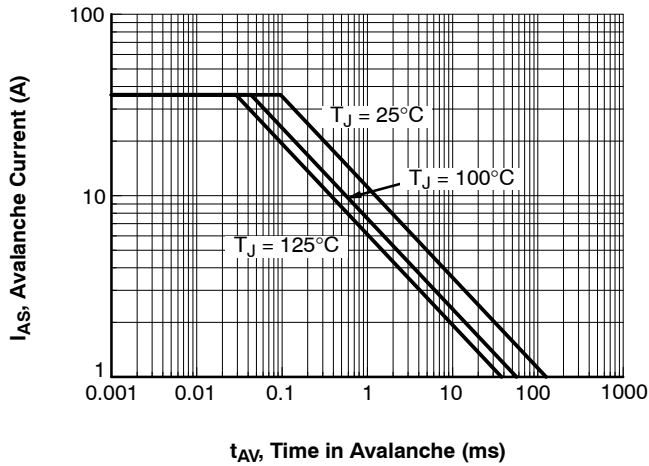


Figure 22. Unclamped Inductive Switching Capability

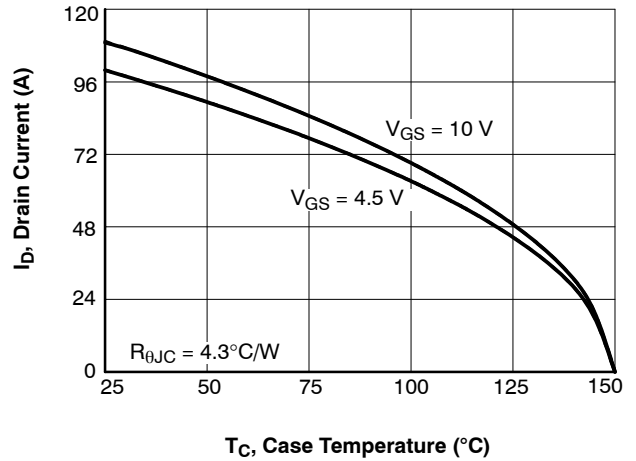


Figure 23. Maximum Continuous Drain Current vs. Case Temperature

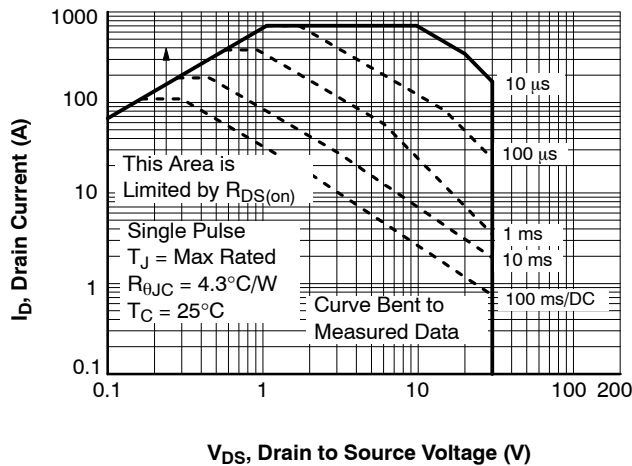


Figure 24. Forward Bias Safe Operating Area

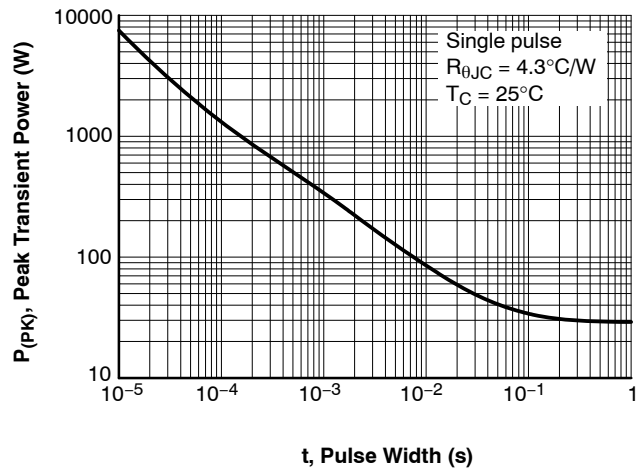
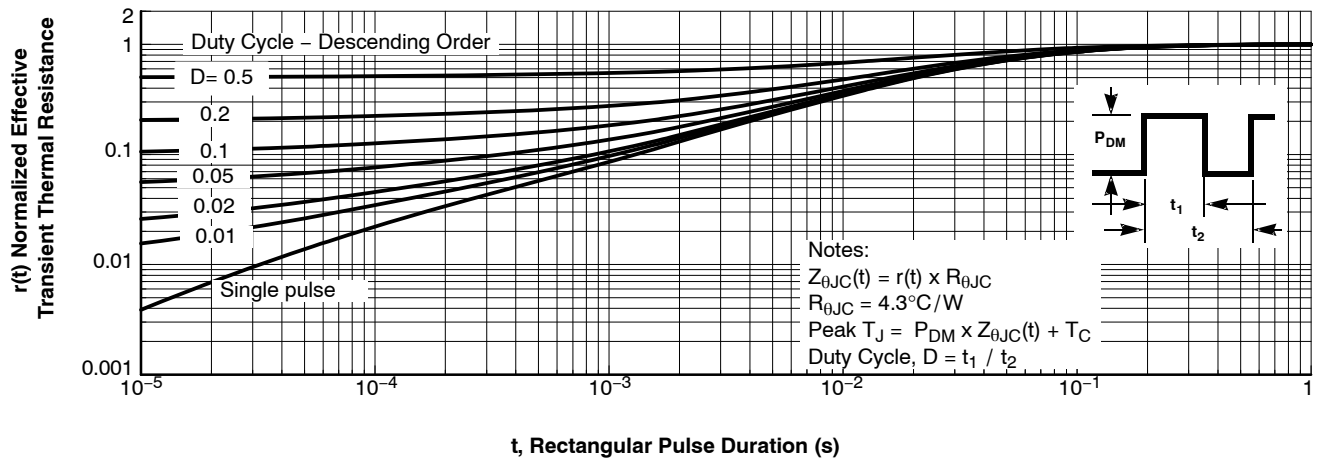


Figure 25. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS (Q2 N-CHANNEL)

(T_J = 25°C unless otherwise noted) (continued)

FDPC5018SG

TYPICAL CHARACTERISTICS (continued)

SyncFET Schottky Body Diode Characteristics

onsemi's SyncFET process embeds a Schottky diode in parallel with POWERTRENCH MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 27 shows the reverse recovery characteristic of the FDPC5018SG.

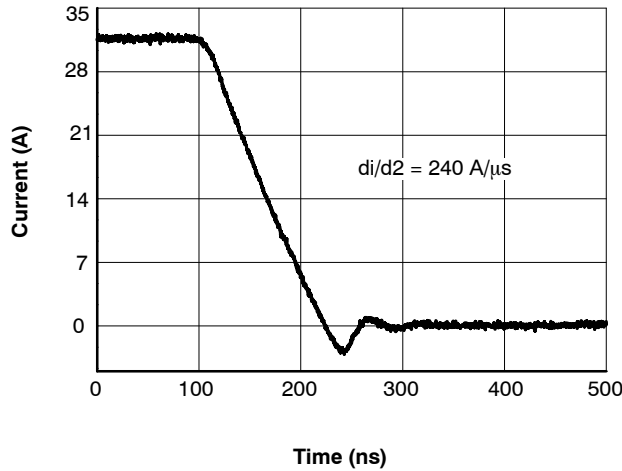


Figure 27. SyncFET Body Diode Reverse Recovery Characteristic

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

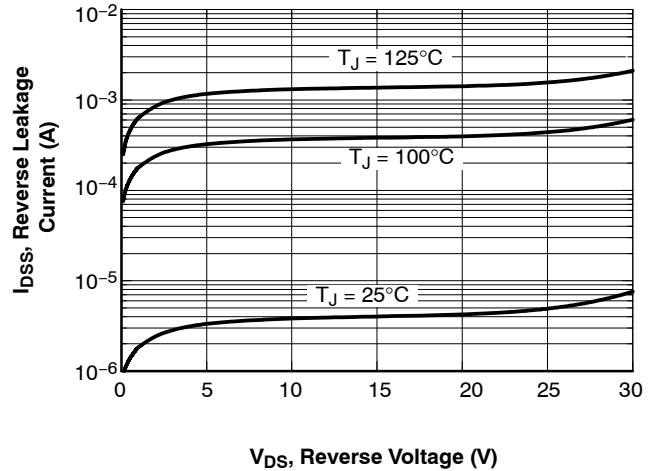
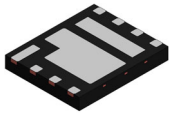


Figure 28. SyncFET Body Diode Reverse Leakage vs. Drain-Source Voltage

PACKAGE MARKING AND ORDERING INFORMATION

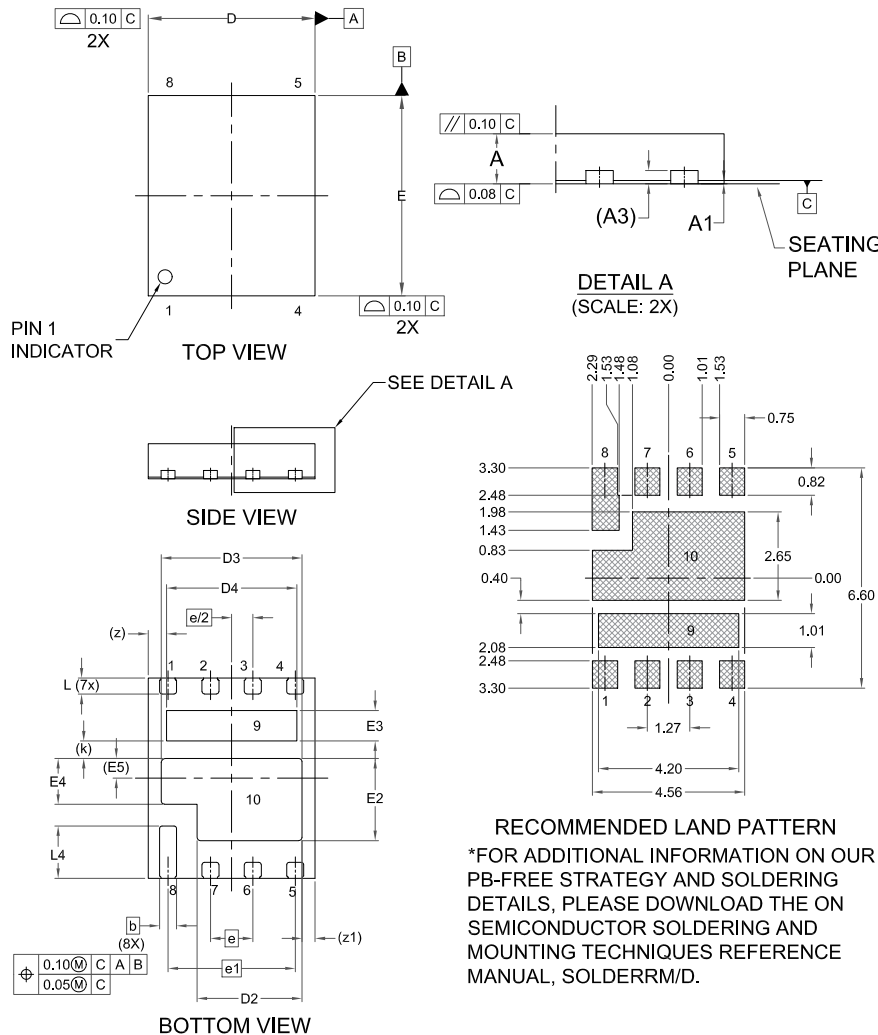
Device	Top Marking	Package	Reel Size	Tape Width	Shipping [†]
FDPC5018SG	FDPC5018SG	Power Clip 56	13"	12 mm	3,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).



PQFN8 5.00x6.00x0.75, 1.27P
CASE 483AR
ISSUE D

DATE 06 NOV 2023



NOTES: UNLESS OTHERWISE SPECIFIED

- A) DOES NOT FULLY CONFORM TO JEDEC REGISTRATION, MO-229, DATED 11/2001.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
A1	0.00	-	0.05
A3	0.20 REF		
b	0.51 BSC		
D	4.90	5.00	5.10
D2	3.05	3.15	3.25
D3	4.12	4.22	4.32
D4	3.80	3.90	4.00
E	5.90	6.00	6.10
E2	2.36	2.46	2.56
E3	0.81	0.91	1.01
E4	1.27	1.37	1.47
E5	0.59 REF		
e	1.27 BSC		
e/2	0.635 BSC		
e1	3.81 BSC		
k	0.52 REF		
L	0.38	0.48	0.58
L4	1.47	1.57	1.67
z	0.55 REF		
z1	0.39 REF		

DOCUMENT NUMBER: 98AON13666G

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DESCRIPTION: PQFN8 5.00x6.00x0.75, 1.27P

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